Memory

也 Units of binary data

- -> Smallest unit = 1 bit
- → 1 byte = 8 bita
- → 1 nibble = 4 bito
- \rightarrow 1 byte = 2 nibblen



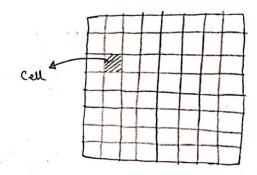
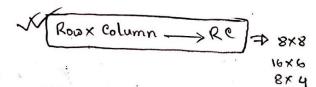


fig: 8×8 bits memory array

or, 1 byte × 1 byte memory onnay

or, 64 bit memory

or, 8 byte memory



田JKb

191KB

= 210 bitn

 $= 1 \times 2^{10} \times 2^{3}$

= 213 bitn

b->bit G-> byte

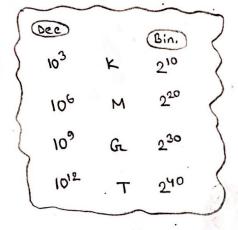
ED 1TB

4D 500 CG

 $= 4 \times 2^{40} \times 2^{3} = 2^{9} \times 2^{30} \times 2^{3}$

= 243 bits

= 242 bitn



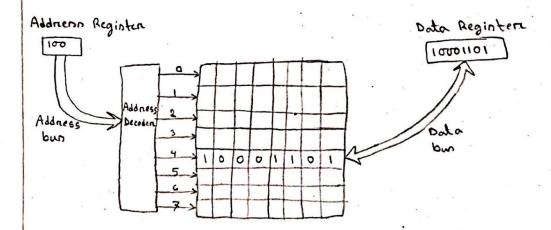
3

Data goen into memorien during a write operation and comer out from memorien during a read operation on a set of lines, in known on data bur.

-> Data bun in bidinectional

Address bus:

For a nead on write operation an address in selected by placing a binary code representing the desired address on a set of lines in Known on address bus.



Write operation:

- 4) Address code "100" in placed on the address but of address "4" in selected.
- 2) Data byte "10001101" in placed on the data bun.
- 3) Write command causes the data byte to be stoned in row "4" (by replacing previous data).

4) Address code "100" in placed on the address bun & address "4" in selected. 3) The content of address "4" in placed on the data bus and shifted into data neginters. A RAM (Random Accept Memory) # Clonification of RAM: RAM Dynamic RAM (DRAM) Static RAM (SRAM) >First Page Mode DRAM

Synchronoun SRAM

(SSRAM)

Asynchronoun GRAM

DOR

Double

(ASRAM)

(FPM DRAM)

(EDO DRAM)

-> Burnt EDO DRAM

(BEDO DRAM)

(SDRAM)

DDR-1

> Extended Data Out DRAM

> Synchronous DRAM

DDR-2

DDR-3

Difference bet SRAM & DRAM

adv. for SRAM connumer lens power than DRAM

SRAM unen flip-flops to stone data wherean DRAM unen capacitors

ods. for Data can be nead much faster from SRAM than from DRAM

adv. for DRAM can stone much more data than bRAM for a given physical

Size of cont.

GRAM VS ROM.

RAM

- → All address are accessible in an equal amount of time and can be selected in any order for a read/write operation
- -> ALL RAMS have both read/write capacity.
- -> RAM lones data when power is off -> volatile memory

ROM (Read only Memory)

- -> Data one stoned permanently on semi-permanently (usually during manufacturing)
- -> Data can only be need from a ROM
- -> ROMs retain stoned data even if power in turned off
 [Non-volatile memory]

Floyd Book Ch-11: Data Storage Cache Memony

- Cache memony in relatively small, high speed memony that

Stonen the most necently used data on instruction from the

larger but slower main (primary) memory.

- Cache memory user BRAM technology

→L1 cache memory

L2 eache memory

⊕ L1 cache: The first level eache is usually integrated in the microprocessor chip and has a very limited storage capacity known as primary cache on L1 eache.

∑ L₂ Cache: The second level cache in a seperate memory
 chip external to the microprocessor and has larger capacity
 but slower compared to L₂ cache, Known as secondary eache
 on L₂ cache.

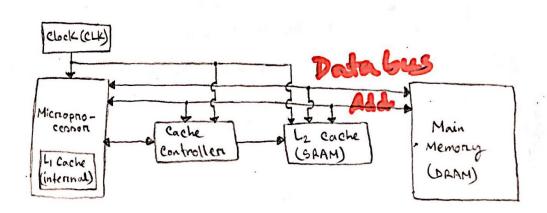


Fig: Block diagram of 4 & Lz cache memory in a computer system.

88 Why refreshing is required in DRAM cell?

Am: DRAMs one boned on capacitan change storage for each bit in the memory armay. This change degrades (leaks off) with time and temperature, so each bit must be periodically refrienced (rechanged) to maintain the connect bit state. Typically, a DRAM must be refreshed every 8 ms to 16 ms, although for some devices the refresh period can exceed 100 ms.

SRAM GT operation (Read & write)